



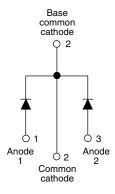
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Vishay Semiconductors

# HEXFRED® Ultrafast Soft Recovery Diode, 2 x 16 A



**TO-247AC** 



PRODUCT SUMMARY	
Package	TO-247AC
I <sub>F(AV)</sub>	2 x 16 A
$V_{R}$	1200 V
V <sub>F</sub> at I <sub>F</sub>	2.3 V
t <sub>rr</sub> typ.	30 ns
T <sub>J</sub> max.	150 °C
Diode variation	Single die

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- Reduced parts count

#### **DESCRIPTION**

VS-HFA32PA120C... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A per leg continuous current, the VS-HFA32PA120C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA32PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	$V_{R}$		1200	V					
Maximum continuous forward current per leg		T 100 °C	16						
per devi	l <sub>F</sub>	T <sub>C</sub> = 100 °C	32	۸					
Single pulse forward current	I <sub>FSM</sub>		190	А					
Maximum repetitive forward current	I <sub>FRM</sub>		64						
Maximum navvar dissination	П	T <sub>C</sub> = 25 °C	151	°C					
Maximum power dissipation	$P_{D}$	T <sub>C</sub> = 100 °C	60	C					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	W					



# VS-HFA32PA120CPbF, VS-HFA32PA120C-N3

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<b>ELECTRICAL SPECIFICATIONS PER LEG</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-				
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 16 A		-	2.5	3.0	V		
		I <sub>F</sub> = 32 A	See fig. 1	-	3.2	3.93			
		I <sub>F</sub> = 16 A, T <sub>J</sub> = 125 °C		-	2.3	2.7			
Maximum reverse	_	$V_R = V_R$ rated See fig. 2		-	0.75	20			
leakage current		$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See lig. 2	-	375	2000	μA		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V See fig. 3		=	27	40	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nΗ		

<b>DYNAMIC RECOVERY CHARACTERISTICS PER LEG</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time See fig. 5, 10	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	30	-				
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$I_F = 16 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	90	135	ns			
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	164	245				
Peak recovery current See fig. 6	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	5.8	10	A nC			
	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	8.3	15				
Reverse recovery charge See fig. 7	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	260	675				
	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	680	1838	IIC			
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	120	-	Λ/μο			
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	76	_	- A/μs			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	0.83				
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W			
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.50	-				
Weight			-	2.0	-	g			
vveigni			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-247AC (JEDEC)	HFA32PA120C						

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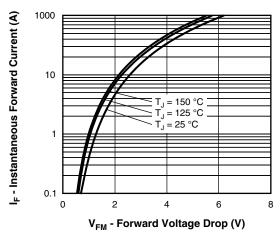


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

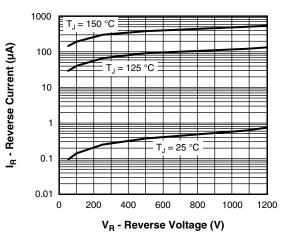


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

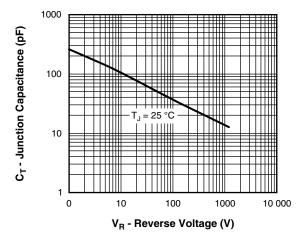


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

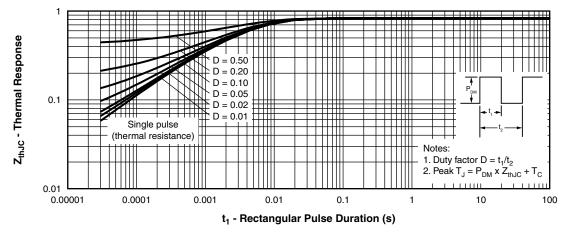


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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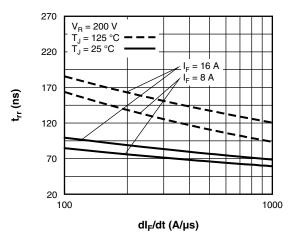


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>E</sub>/dt (Per Leg)

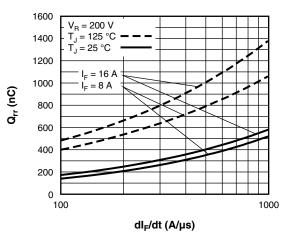


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt (Per Leg)

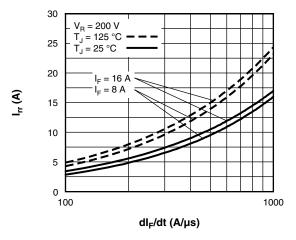


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt (Per Leg)

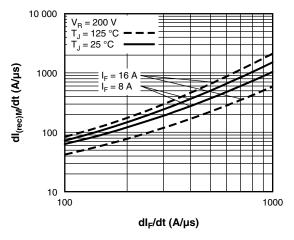


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt (Per Leg)

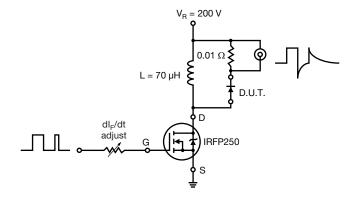
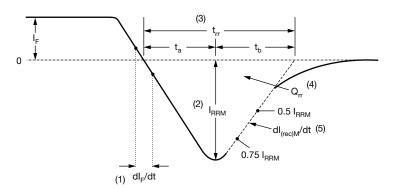


Fig. 9 - Reverse Recovery Parameter Test Circuit

## VS-HFA32PA120CPbF, VS-HFA32PA120C-N3

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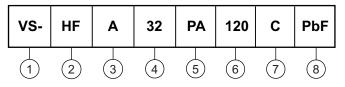


- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (2) I<sub>RRM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (5) dl<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

Device code



- Vishay Semiconductors product
- HEXFRED<sup>®</sup> family
- 3 Electron irradiated
- Current rating (32 = 32 A)
- **5** PA = TO-247AC
- 6 Voltage rating: (120 = 1200 V)
- Circuit configuration
  C = common cathode
- 8 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-HFA32PA120CPbF	25	500	Antistatic plastic tube							
VS-HFA32PA120C-N3	25	500	Antistatic plastic tube							

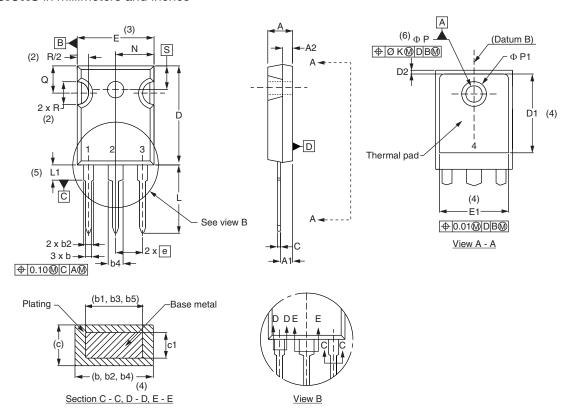
LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95542					
Part marking information	TO-247ACPbF	www.vishay.com/doc?95226					
	TO-247AC-N3	www.vishay.com/doc?95007					



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## TO-247 - 50 mils L/F

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES		NOTES S	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØΚ	0.2	254	0.0	)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			Ν	7.62	BSC	0.3		
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	'BSC	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- $^{(7)}$  Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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